

AMENDMENTS TO THE SPECIFICATION

On page 40, please amend the paragraph beginning at line 16 as follows:

Referring to Fig. 14, a nitride-base semiconductor laser diode according to a fourth embodiment of the present invention is provided with no n-type optical guide layer 42 24 dissimilarly to the aforementioned second embodiment. The remaining structure of the further embodiment is similar to that of the second embodiment.